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Bibliographic data: JP 2006504278 (A)

NON-VOLATILE MEMORY CELL, MEMORY CELL ARRANGEMENT AND METHOD FOR PRODUCTION OF A NON-VOLATILE MEMORY CELL

Publication date:

2006-02-02

Inventor(s):

Applicant(s):

C01B31/02; G11C13/02; H01L21/28; H01L21/336; H01L21/8246;

H01L21/8247; H01L21/84; H01L27/10; H01L27/115; H01L27/12;

H01L29/08; H01L29/786; H01L29/788; H01L29/792; H01L27/28;

H01L51/00; H01L51/30

Classification:

International: H01L27/10; G11C13/02; H01L21/28G; H01L21/336G; H01L21/84;

H01L27/115; H01L27/115G4; H01L27/128; H01L29/786G;

H01L29/792; H01L51/00G2B

Application number:

JP2004054743T 20031029

Priority number(s):

DE20021050829 20021031; WO2003DE03588 20031029

- WO 2004040867 (A1)
- US 2006011972 (A1)
- US 7266376 (B2)
- EP 1686067 (A1)
- DE 10250829 (A1)
- more

Also published as:

Abstract not available for JP 2006504278 (A)

Abstract of corresponding document:

WO 2004040867 (A1)

The invention relates to a non-volatile memory cell, memory cell arrangement and method for production of a non-volatile memory cell. The non-volatile memory cell comprises a vertical field-effect transistor, with a nanoelement arranged as channel region and an electrical insulating layer at least partly surrounding the nanoelement as charge storage layer and as gate-insulating layer. The above is arranged such that electric charge carriers may be selectively introduced into or removed from the above and the electrical conductivity characteristics of the nanoelement may be influenced by the electrical charge carriers introduced into electrical insulating layer.

